

In the Specification

At page 1, before the Technical Field insert:

CROSS REFERENCE TO RELATED APPLICATION

This patent application is a Continuation Application of U.S. Patent Application Serial No. 10/128,933 filed April 23, 2002, entitled "Semiconductor Processing Methods Of Forming A Contact Opening To A Conductive Line and Methods of Forming Substrate Active Area Source/Drain Regions," naming Werner Juengling as inventor, which is a Continuation of U.S. Patent Application Serial No. 09/141,777 filed August 27, 1998, now U.S. Patent No. 6,395,623 B1 which issued May 28, 2002, the disclosures of which are hereby incorporated herein by reference.

Amend the paragraph beginning on page 8, line 5, and extending through p. 8, line 12, as follows:

Referring to Figs. 3 and 4, a layer of photoresist 42 is formed over semiconductive substrate 10 (Fig. 3) and subsequently patterned (Fig. 4) to form or define a doping window 44 over PMOS active region 14, and ~~a contact~~ an opening 46 over conductive line 24. In the illustrated and preferred embodiment, doping window 44 has a first open lateral width dimension W_1 and ~~contact~~ opening 46 has a second open lateral width dimension W_2 . Second open lateral width dimension W_2 is less than the first open lateral width dimension W_1 .